



Docket No.: R2184.0282  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Hirokazu Iwata et al.

Application No.: 10/765,502

Confirmation No.: 2556

Filed: January 28, 2004

Art Unit: 1722

For: METHOD OF GROWING GROUP III  
NITRIDE CRYSTAL, GROUP III NITRIDE  
CRYSTAL GROWN THEREBY, GROUP III  
NITRIDE CRYSTAL GROWING  
APPARATUS AND SEMICONDUCTOR  
DEVICE

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Examiner: R. Kunemund

**AMENDMENT IN RESPONSE TO RESTRICTION REQUIREMENT**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In response to the restriction requirement in the Office Action mailed April 21, 2006, Applicants provisionally elect Group 1, claims 1-14 and 18-25, for continued examination, with traverse.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 11 of this paper.